






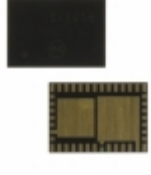

|   |   |
|---|---|
|  | <h2>SI1013X-T1-E3</h2>  |
|   | <p><b>Hersteller-Teilenummer:</b> SI1013X-T1-E3</p> <p><b>Hersteller / Marke:</b> Electro-Films (EFI) / Vishay</p> <p><b>Teil der Beschreibung:</b> MOSFET P-CH 20V 350MA SC89-3</p> <p><b>Datenblätter:</b>  <a href="#">SI1013X-T1-E3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 77445 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation.<br/>See specs for product details.</p>            |   |

### Spezifikationen

|  |   |
|--|---|
| Teilenummer                                      | SI1013X-T1-E3   |
| Hersteller                                       | Electro-Films (EFI) / Vishay  |
| Beschreibung                                     | MOSFET P-CH 20V 350MA SC89-3  |
| Kategorie  | <a href="#">Diskrete Halbleiterprodukte</a> > <a href="#">Transistoren-FETs</a> , |
| Teilstatus                                       | 77445 pcs Stock   |
| detaillierte Beschreibung                        | P-Channel 20V 350mA (Ta) 250mW (Ta) Surface                                       |
| Serie  | TrenchFET®  |
| Technologie                                      | MOSFET (Metal Oxide)  |
| Betriebstemperatur                               | -55°C ~ 150°C (TJ)  |
| Befestigungsart                                  | Surface Mount   |
| Verpackung / Gehäuse                             | SC-89, SOT-490  |
| Supplier Device-Gehäuse                          | SC-89-3   |
| Verlustleistung (max)                            | 250mW (Ta)  |
| Typ FET  | P-Channel   |
| FET-Merkmal                                      | -   |
| Drain-Source-Spannung (Vdss)                     | 20V   |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 350mA (Ta)  |
| Rds On (Max) @ Id, Vgs                           | 1.2 Ohm @ 350mA, 4.5V   |
| VGS (th) (Max) @ Id                              | 450mV @ 250µA (Min)   |
| Gate Charge (Qg) (Max) @ Vgs                     | 1.5nC @ 4.5V  |
| Antriebsspannung (Max Rds On, Min Rds On)        | 1.8V, 4.5V  |
| Vgs (Max)  | ±6V   |
| Verpackung                                       | Tape & Reel (TR)  |
| Bleifreier Status / RoHS-Status                  | Lead free / RoHS Compliant  |
| Feuchtigkeitsempfindlichkeitsniveau (MSL)        | 1 (Unlimited)   |
| Andere Namen                                     | SI1013X-T1-E3TR   |

SI1013X-T1-E3 ist neu im Original, Suche SI1013X-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1013X-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI1013X-T1-E3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

|  |  |   |  |
|--|--|---|--|
|  <p><b>SI1013X</b><br/>VISHAY<br/>SI1013X VISHAY</p>                                  |  <p><b>SI1013R-T1-GE3</b><br/>Vishay / Siliconix<br/>MOSFET P-CH 20V 350MA SC-75A</p>               |  <p><b>SI1014-C-GM2</b><br/>Energy Micro (Silicon Labs)<br/>IC RF TXRX+MCU ISM&lt;1GHZ 42-VFLGA</p> |  <p><b>SI1013R-T1-GE3</b><br/>Electro-Films (EFI) / Vishay<br/>MOSFET P-CH 20V 350MA SC-75A</p> |
|  <p><b>SI1013X-T1-GE3</b><br/>Vishay / Siliconix<br/>MOSFET P-CH 20V 350MA SC89-3</p> |  <p><b>SI1014-A-GMR</b><br/>Energy Micro (Silicon Labs)<br/>IC RF TXRX+MCU ISM&lt;1GHZ 42-WFQFN</p> |  <p><b>SI1014-A-GM</b><br/>Energy Micro (Silicon Labs)<br/>IC RF TXRX+MCU ISM&lt;1GHZ 42-WFQFN</p>  |  <p><b>SI1013X-T1-E3</b><br/>Vishay / Siliconix<br/>MOSFET P-CH 20V 350MA SC89-3</p>            |

### heiße Teile

Mehr

|                 |                 |                 |                 |                 |
|-----------------|-----------------|-----------------|-----------------|-----------------|
| SI1000-C-GM     | SI1002-C-GMR    | SI1003-C-GM     | SI1011X-T1-GE3  | SI1011X-T1-GE3  |
| SI1012CR-T1-GE3 | SI1012CR-T1-GE3 | SI1012R-T1      | SI1012R-T1-E3   | SI1012R-T1-E3   |
| SI1012R-T1-GE3  | SI1012R-T1-GE3  | SI1012X-T1      | SI1012X-T1-E3   | SI1012X-T1-E3   |
| SI1012X-T1-GE3  | SI1012X-T1-GE3  | SI1013CX-T1-GE3 | SI1013CX-T1-GE3 | SI1013R-T1      |
| SI1013R-T1-E3   | SI1013R-T1-E3   | SI1013R-T1-GE3  | SI1013R-T1-GE3  | SI1013X-T1      |
| SI1013X-T1-E3   | SI1013X-T1-GE3  | SI1013X-T1-GE3  | SI1016CX-T1-GE3 | SI1016CX-T1-GE3 |
| SI1016X-T1-E3   | SI1016X-T1-E3   | SI1016X-T1-GE3  | SI1016X-T1-GE3  | SI1016X2-T1-GE3 |
| SI1021R-T1      | SI1021R-T1-E3   | SI1021R-T1-E3   | SI1022R-T1      | SI1022R-T1-E3   |
| SI1022R-T1-E3   | SI1022R-T1-GE3  | SI1022R-T1-GE3  | SI1022R-TI-E3   | SI1023CX-T1-GE3 |
| SI1023CX-T1-GE3 | SI1023X-T1      | SI1023X-T1-E3   | SI1023X-T1-E3   | SI1023X-T1-GE3  |

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